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ON Semiconductor
MBR3045ST

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MBR3045ST, MBRB3045CT-1

Switch-mode Power Rectifier

ON Semiconductor™

http://onsemi.com

SCHOTTKY BARRIER RECTIFIER 30 AMPERES 45 VOLTS

Features and Benefits

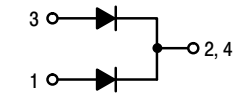
- Dual Diode Construction − Terminals 1 and 3 May Be Connected for Parallel Operation at Full Rating
- 45 V Blocking Voltage
- Low Forward Voltage Drop
- 175°C Operating Junction Temperature
- These are Pb-Free Devices

Applications

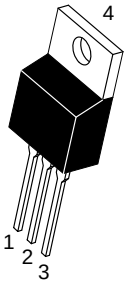
- Power Supply − Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

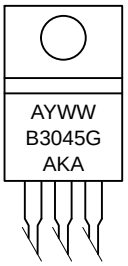
- Case: Epoxy, Molded
- Weight (Approximately): 1.9 Grams (TO−220)
  1.5 Grams (TO−262)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Epoxy Meets UL 94 V−0 @ 0.125 in

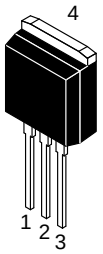


MARKING DIAGRAMS

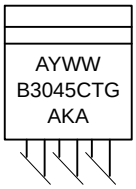


TO−220
CASE 221A
STYLE 6





I²PAK (TO−262)
CASE 418D
STYLE 3



A	= Assembly Location
Y	= Year
WW	= Work Week
AKA	= Polarity Designator
G	= Pb−Free Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	45	V
Average Rectified Current (Per Device / Per Diode) (T_C = 130°C)	$I_{F(AV)}$	30 15	A
Peak Repetitive Forward Current, per Diode (Square Wave, V_R = 45 V, 20 kHz)	I_{FRM}	30	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions, Halfwave, Single Phase, 60 Hz)	I_{FSM}	150	A
Peak Repetitive Reverse Current, per Diode (2.0 μs, 1.0 kHz)	I_{RRM}	2.0	A
Storage Temperature Range	T_{stg}	−65 to +175	°C
Operating Junction Temperature (Note 1)	T_J	−65 to +175	°C
Peak Surge Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

THERMAL CHARACTERISTICS (Per Diode)

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	°C/W

ELECTRICAL CHARACTERISTICS (Per Diode)

Characteristic	Symbol	Value	Unit
Instantaneous Forward Voltage (Note 2) (i_F = 15 Amp, T_C = 25°C) (i_F = 15 Amp, T_C = 125°C) (i_F = 30 Amp, T_C = 25°C) (i_F = 30 Amp, T_C = 125°C)	v_F	 0.62 0.57 0.76 0.72	V
Instantaneous Reverse Current (Note 2) (V_R = 45 Volts, T_C = 25°C) (V_R = 45 Volts, T_C = 125°C)	I_R	 0.2 40	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2 Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

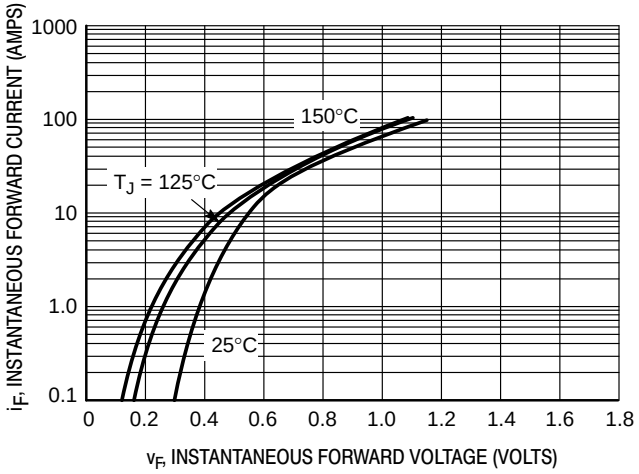


Figure 1. Typical Forward Voltage

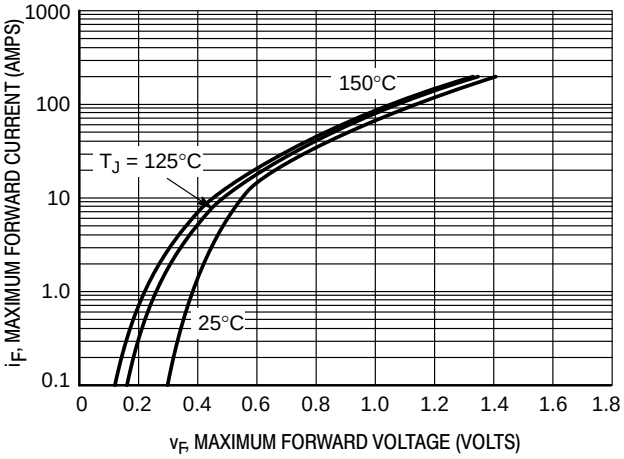


Figure 2. Maximum Reverse Current

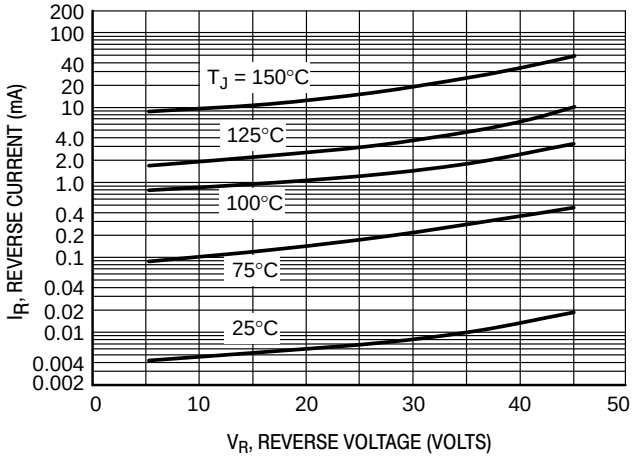


Figure 3. Typical Reverse Current

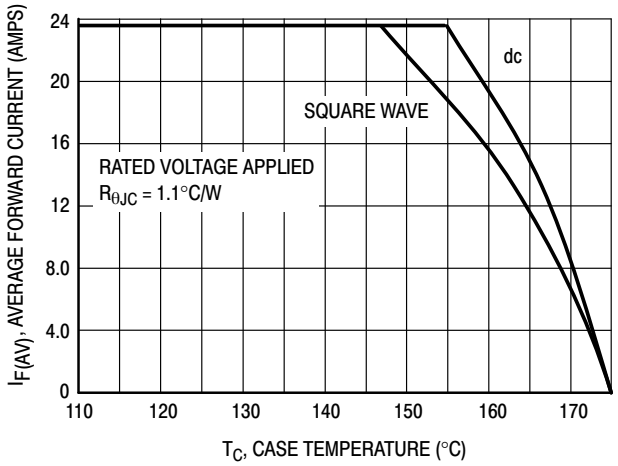


Figure 4. Current Derating, Case

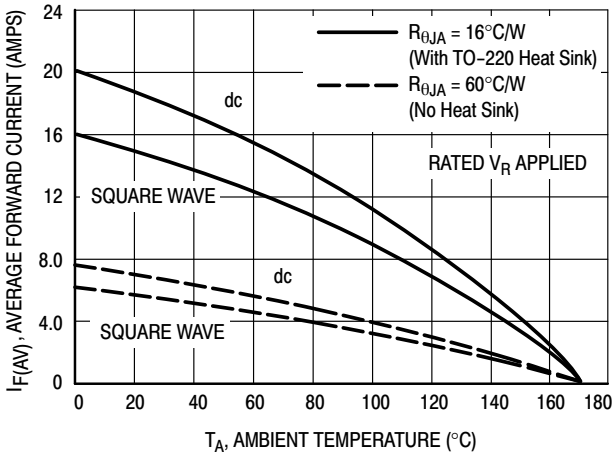


Figure 5. Current Derating, Ambient

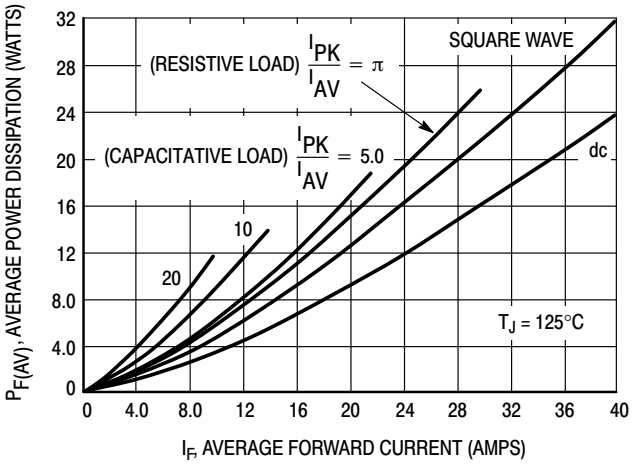


Figure 6. Forward Power Dissipation

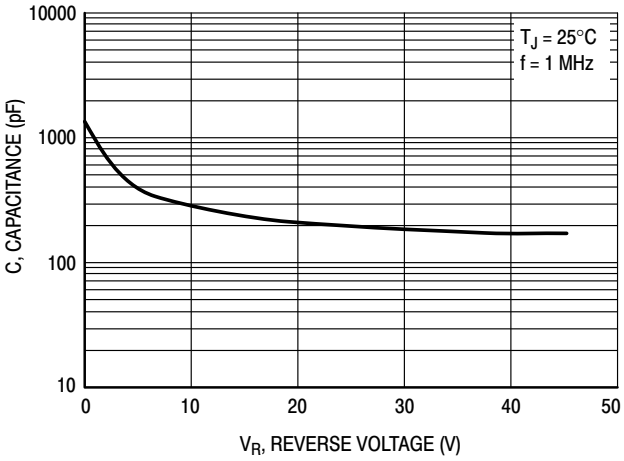


Figure 7. Capacitance

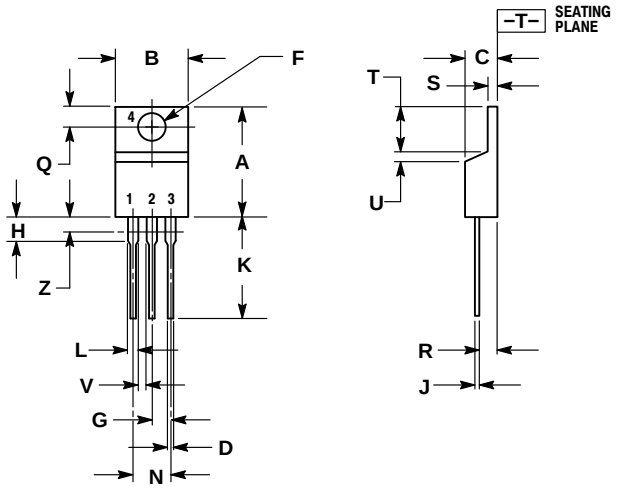
ORDERING INFORMATION

Device	Package	Shipping
MBR3045STG	TO−220 (Pb−Free)	50 Units/Rail
MBRB3045CT−1G	TO−262 (Pb−Free)	50 Units/Rail

MBR3045ST, MBRB3045CT−1

PACKAGE DIMENSIONS

TO−220
CASE 221A−09
ISSUE AH



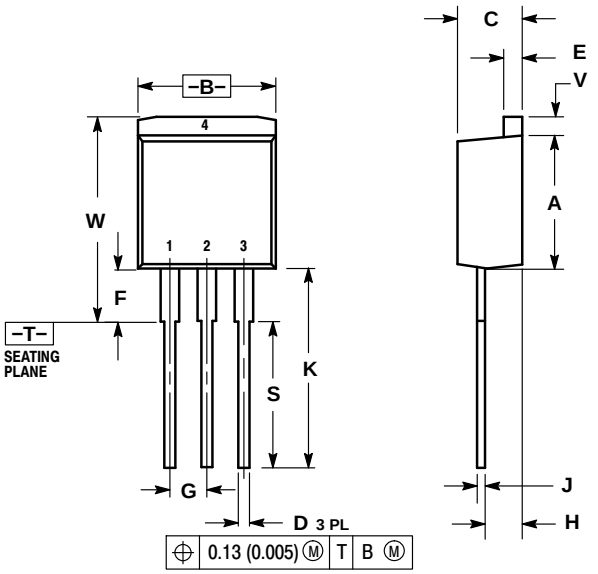
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

PACKAGE DIMENSIONS

I²PAK (TO−262)
CASE 418D
ISSUE D



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.335	0.380	8.51	9.65
B	0.380	0.406	9.65	10.31
C	0.160	0.185	4.06	4.70
D	0.026	0.035	0.66	0.89
E	0.045	0.055	1.14	1.40
F	0.122 REF		3.10 REF	
G	0.100 BSC		2.54 BSC	
H	0.094	0.110	2.39	2.79
J	0.013	0.025	0.33	0.64
K	0.500	0.562	12.70	14.27
S	0.390 REF		9.90 REF	
V	0.045	0.070	1.14	1.78
W	0.522	0.551	13.25	14.00

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

PUBLICATION ORDERING INFORMATION

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